

# GSM2324

## 100V N-Channel Enhancement Mode MOSFET

### Product Description

GSM2324, N-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent  $R_{DS(ON)}$ , low gate charge.

These devices are particularly suited for low voltage power management, such as smart phone and notebook computer and other battery powered circuits, and low in-line power loss are needed in commercial industrial surface mount applications.

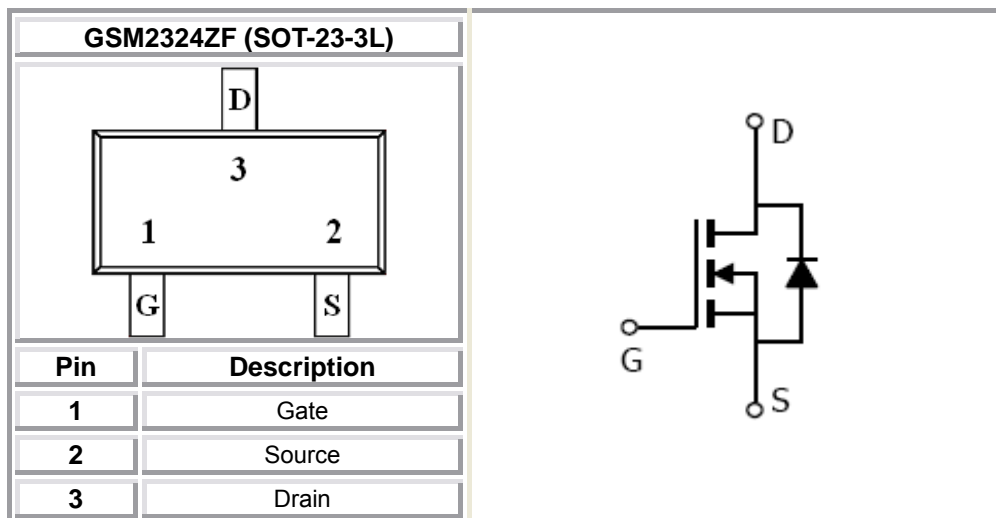
### Features

- 100V/2.3A,  $R_{DS(ON)}=285m\Omega@V_{GS}=10V$
- 100V/1.8A,  $R_{DS(ON)}=295m\Omega@V_{GS}=4.5V$
- Super high density cell design for extremely low  $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- SOT-23-3L package design

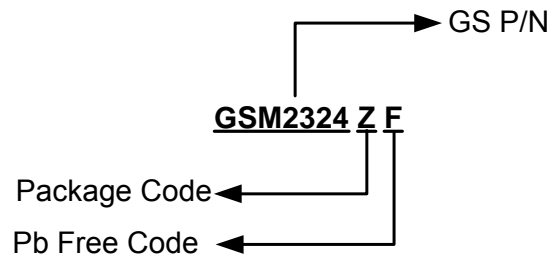
### Applications

- DC/DC Converters
- Load Switch
- LED Backlighting in LCD TVs

### Packages & Pin Assignments

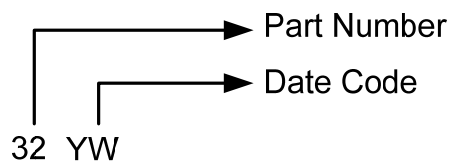


## Ordering Information



Part Number	Package	Quantity Reel
GSM2324ZF	SOT-23-3L	3000 PCS

## Marking Information



## Absolute Maximum Ratings

(T<sub>A</sub>=25°C unless otherwise noted)

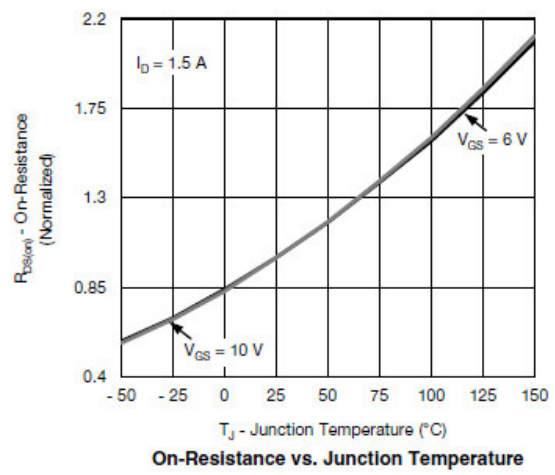
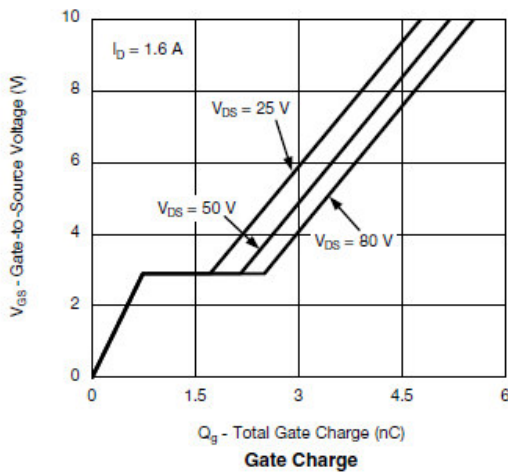
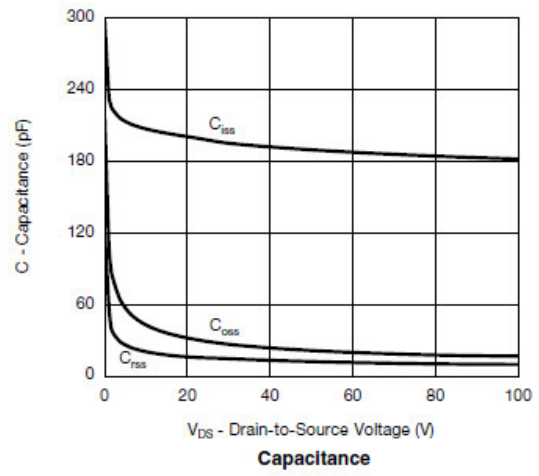
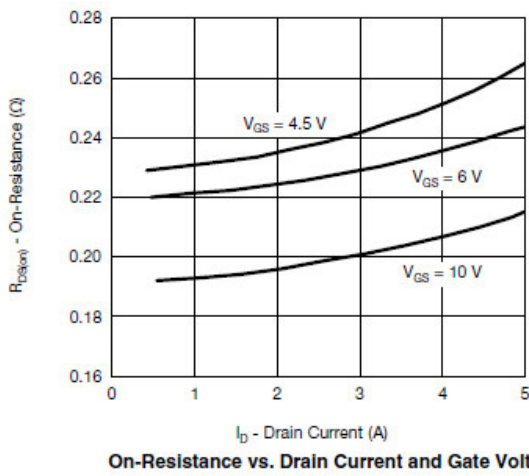
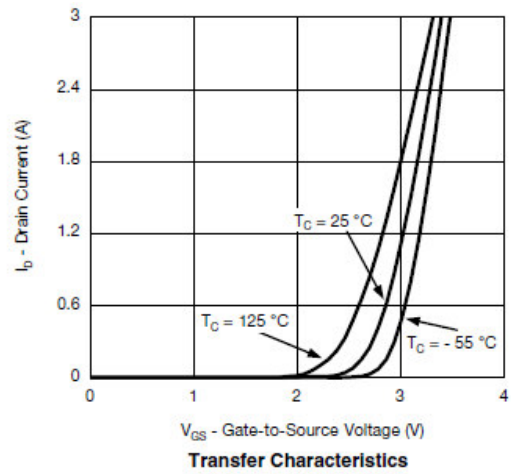
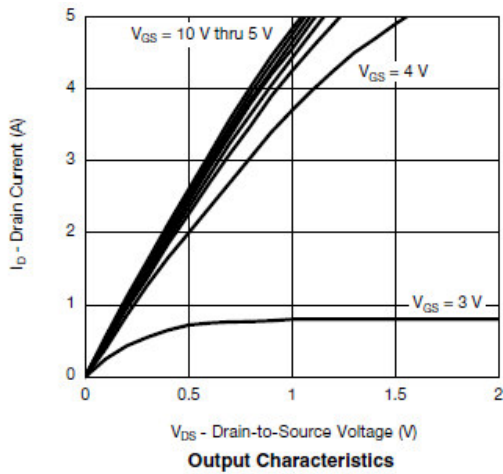
Symbol	Parameter	Typical	Unit
V <sub>DSS</sub>	Drain-Source Voltage	100	V
V <sub>GSS</sub>	Gate –Source Voltage	±20	V
I <sub>D</sub>	Continuous Drain Current(T <sub>J</sub> =150°C)	T <sub>A</sub> =25°C	2.3
		T <sub>A</sub> =70°C	1.8
I <sub>DM</sub>	Pulsed Drain Current	5	A
I <sub>S</sub>	Continuous Source Current(Diode Conduction)	1.6	A
P <sub>D</sub>	Power Dissipation	T <sub>A</sub> =25°C	1.25
		T <sub>A</sub> =70°C	0.8
T <sub>J</sub>	Operating Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature Range	-55/150	°C
R <sub>θJA</sub>	Thermal Resistance-Junction to Ambient	120	°C/W

## Electrical Characteristics

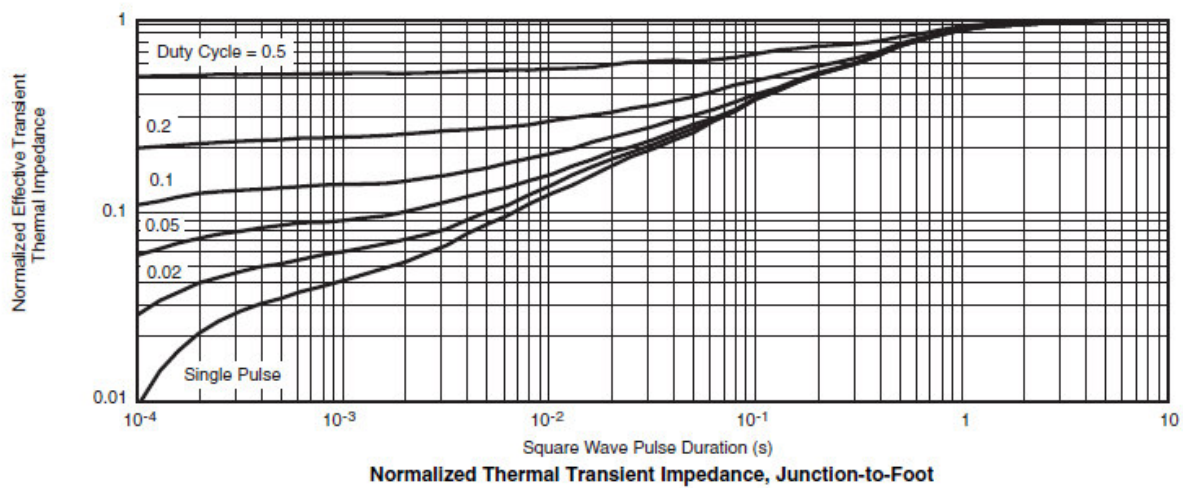
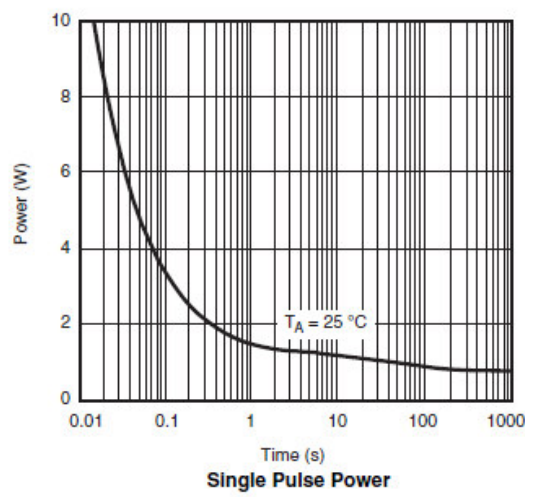
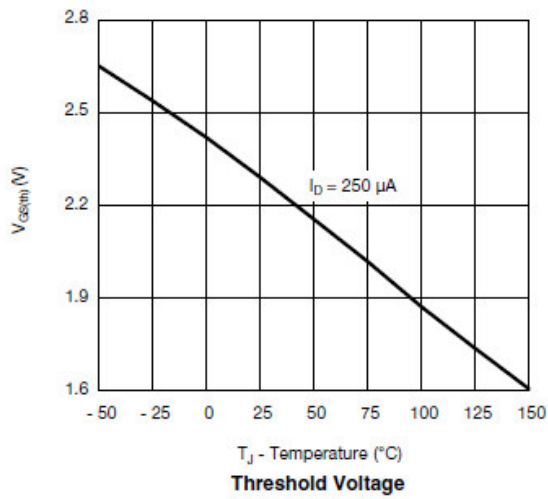
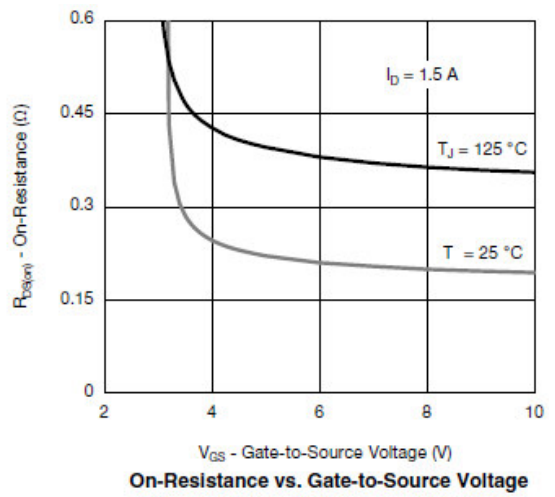
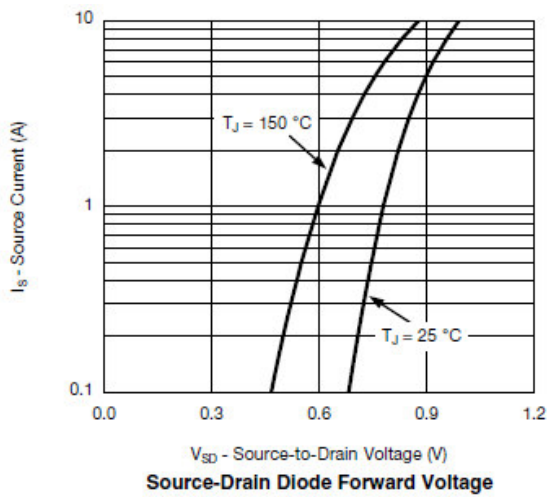
(T<sub>A</sub>=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static</b>						
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	100			V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1.0		2.0	
I <sub>GSS</sub>	Gate Leakage Current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±100	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =80V, V <sub>GS</sub> =0V			1	μA
		V <sub>DS</sub> =80V, V <sub>GS</sub> =0V, T <sub>J</sub> =85°C			10	
I <sub>D(on)</sub>	On-State Drain Current	V <sub>DS</sub> ≥5V, V <sub>GS</sub> =4.5V	5			A
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =2.3A		265	285	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =1.8A		275	295	
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =20V, I <sub>D</sub> =1.5A		2		S
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =1.3A, V <sub>GS</sub> =0V		0.85	1.2	V
<b>Dynamic</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =50V, V <sub>GS</sub> =0V, f=1MHz		200		pF
C <sub>oss</sub>	Output Capacitance			22		
C <sub>rss</sub>	Reverse Transfer Capacitance			13		
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =50V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =1.6A		2.8	5.8	nC
Q <sub>gs</sub>	Gate-Source Charge			0.75		
Q <sub>gd</sub>	Gate-Drain Charge			1.4		
t <sub>d(on)</sub>	Turn-On Time	V <sub>DD</sub> =50V, R <sub>L</sub> =39Ω, I <sub>D</sub> =1.3A, V <sub>GEN</sub> =4.5V, R <sub>G</sub> =1Ω		25	50	ns
t <sub>r</sub>				20	50	
t <sub>d(off)</sub>	Turn-Off Time			15	30	
t <sub>f</sub>				10	25	

## Typical Performance Characteristics

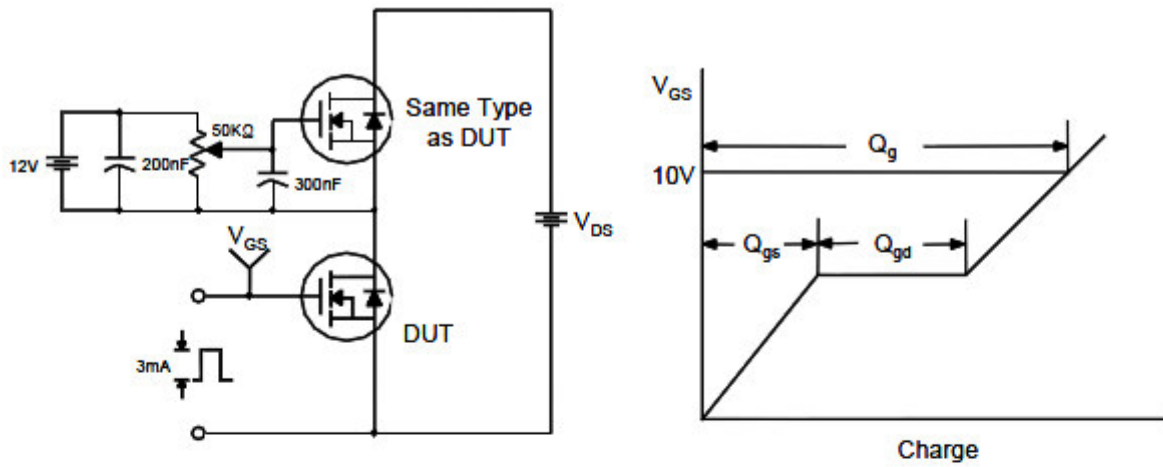


## Typical Performance Characteristics (continue)

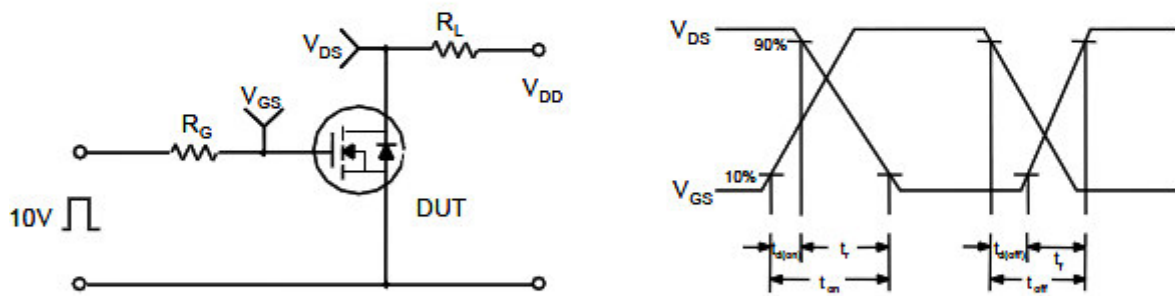


## Typical Performance Characteristics (continue)

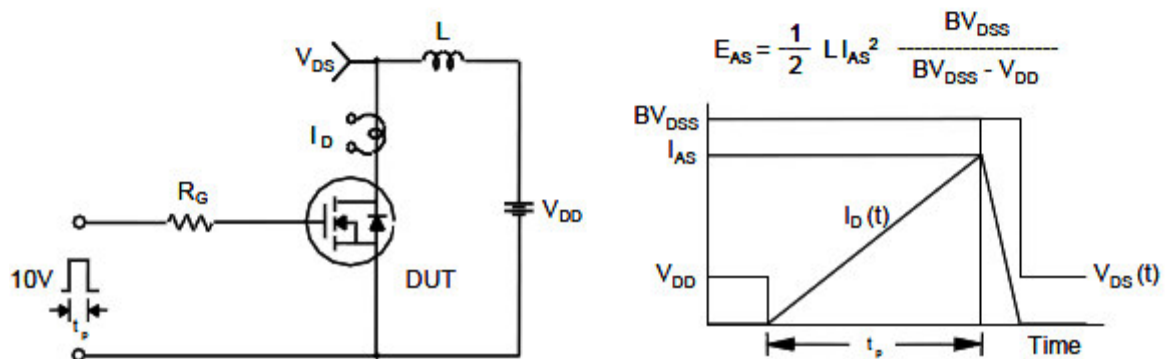
### Gate Charge Test Circuit & Waveform



### Resistive Switching Test Circuit & Waveforms

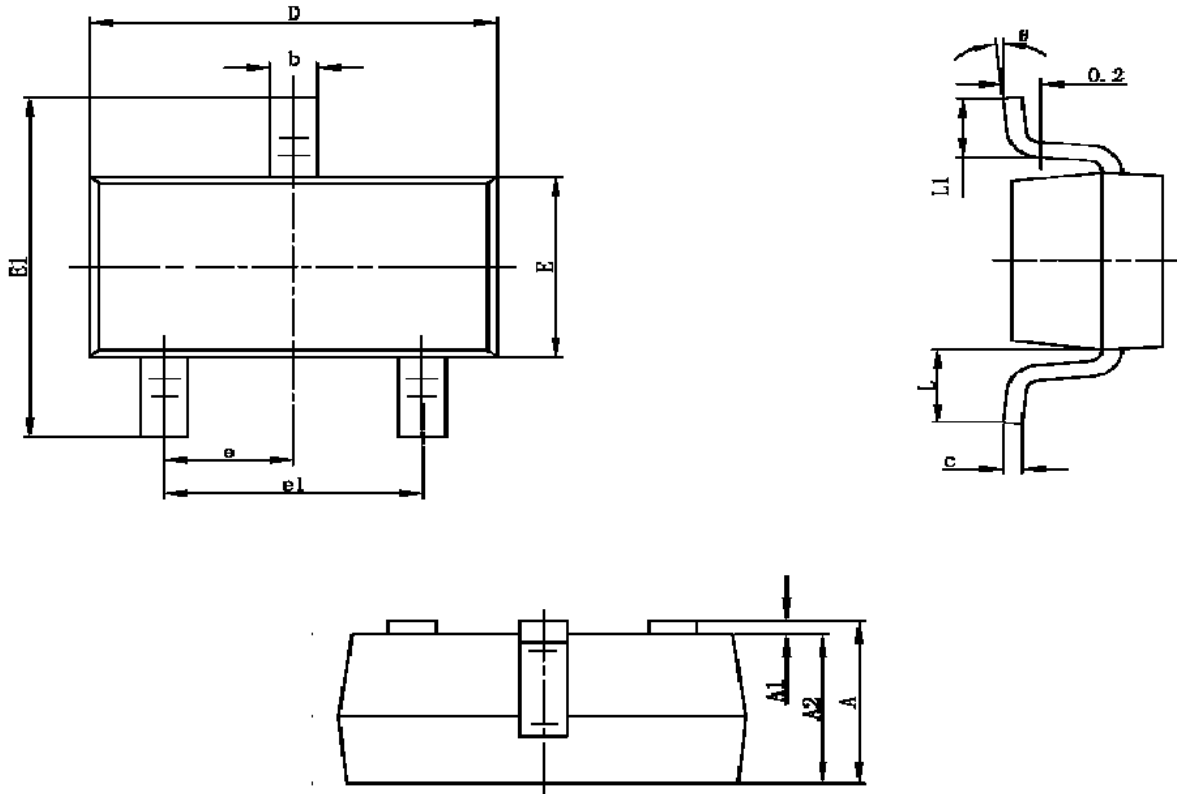


### Unclamped Inductive Switching Test Circuit & Waveforms



## Package Dimension

### SOT-23-3L PLASTIC PACKAGE







Dimensions				
SYMBOL	Millimeters		Inches	
	MIN	MAX	MIN	MAX
A	1.05	1.25	0.041	0.049
A1	0	0.1	0	0.004
A2	1.05	1.15	0.041	0.045
b	0.3	0.4	0.012	0.016
c	0.1	0.2	0.004	0.008
D	2.82	3.02	0.111	0.119
E	1.5	1.7	0.059	0.067
E1	2.65	2.95	0.104	0.116
e	0.950 (TYP)		0.037 (TYP)	
e1	1.8	2	0.071	0.079
L	0.700 (REF)		0.028 (REF)	
L1	0.3	0.6	0.012	0.024
Q	0°	8°	0°	8°





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## CONTACT US

GS Headquarter	
	4F.,No.43-1,Lane11,Sec.6,Minquan E.Rd Neihu District Taipei City 114, Taiwan (R.O.C)
	886-2-2657-9980
	886-2-2657-3630
	sales_twn@gs-power.com

Wu-Xi Branch	
	No.21 Changjiang Rd., WND, Wuxi, Jiangsu, China (INFO. &. TECH. Science Park Building A 210 Room)
	86-510-85217051
	86-510-85211238
	sales_cn@gs-power.com

RD Division	
	824 Bolton Drive Milpitas. CA. 95035
	1-408-457-0587